BAV70L, SBAV70L

Dual Switching Diode Common Cathode

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (EACH DIODE)

| Rating | Symbol | Value | Unit |
|---|------------------|--|------|
| Reverse Voltage | V _R | 100 | V |
| Forward Current | ١ _F | 200 | mA |
| Repetitive Peak Forward Current (Pulse Wave = 1 sec, Duty Cycle = 66%) | I _{FRM} | 1.5 | A |
| Non-Repetitive Peak Forward Current (Square Wave, $T_J = 25^{\circ}C$ prior to surge) $t = 1 \ \mu s$ $t = 10 \ \mu s$ $t = 100 \ \mu s$ $t = 1 \ m s$ $t = 10 \ m s$ $t = 100 \ m s$ $t = 1 \ s$ | I _{FSM} | 31 16 10 4.5 2.5 1.0 0.5 | A |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|---|-----------------------------------|----------------|-------------|
| Total Device Dissipation FR-5 Board (Note 1) T _A = 25°C Derate above 25°C | P _D | 225 1.8 | mW mW/°C |
| Thermal Resistance, Junction-to-Ambient | R_{\thetaJA} | 556 | °C/W |
| Total Device Dissipation Alumina Substrate, (Note 2) T _A = 25°C Derate above 25°C | P _D | 300 2.4 | mW mW/°C |
| Thermal Resistance, Junction-to-Ambient | R_{\thetaJA} | 417 | °C/W |
| Junction and Storage Temperature | T _J , T _{stg} | –55 to +150 | °C |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.

2. Alumina = 0.4 \times 0.3 \times 0.024 in. 99.5% alumina.

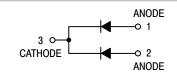


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MARKING DIAGRAM



A4 = Device Code M = Date Code* • = Pb-Free Package

(Note: Microdot may be in either location) *Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

| Device | Package | Shipping [†] |
|------------|---------------------|-----------------------|
| BAV70LT1G | SOT-23 (Pb-Free) | 3,000 / Tape & Reel |
| SBAV70LT1G | SOT-23 (Pb-Free) | 3,000 / Tape & Reel |
| BAV70LT3G | SOT-23 (Pb-Free) | 10,000 / Tape & Reel |
| SBAV70LT3G | SOT-23 (Pb-Free) | 10,000 / Tape & Reel |

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

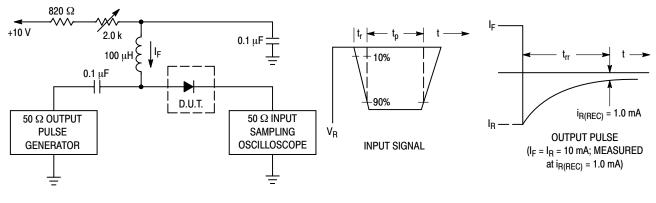
BAV70L, SBAV70L

| ELECTRICAL CHARACTE | ERISTICS (T _A = 25°C unless oth | herwise noted) (Each Diode) |
|---------------------|---|-----------------------------|
|---------------------|---|-----------------------------|

| Characteristic | Symbol | Min | Max | Unit |
|---|-------------------|------------------|----------------------------|------|
| Reverse Breakdown Voltage $(I_{(BR)} = 100 \ \mu A)$ | V _(BR) | 100 | _ | V |
| Reverse Voltage Leakage Current (Note 3) $(V_R = 25 \text{ V}, \text{ T}_J = 150^{\circ}\text{C})$ $(V_R = 100 \text{ V})$ $(V_R = 70 \text{ V}, \text{ T}_J = 150^{\circ}\text{C})$ | I _R | - - - | 60 1.0 100 | μΑ |
| Diode Capacitance ($V_R = 0 V$, f = 1.0 MHz) | CD | _ | 1.5 | pF |
| Forward Voltage $(I_F = 1.0 \text{ mA})$ $(I_F = 10 \text{ mA})$ $(I_F = 50 \text{ mA})$ $(I_F = 150 \text{ mA})$ | V _F | - - - - | 715 855 1000 1250 | mV |
| Reverse Recovery Time $R_L = 100 \Omega$ (I _F = I _R = 10 mA, I _{R(REC)} = 1.0 mA) (Figure 1) | t _{rr} | _ | 6.0 | ns |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. For each individual diode while second diode is unbiased.



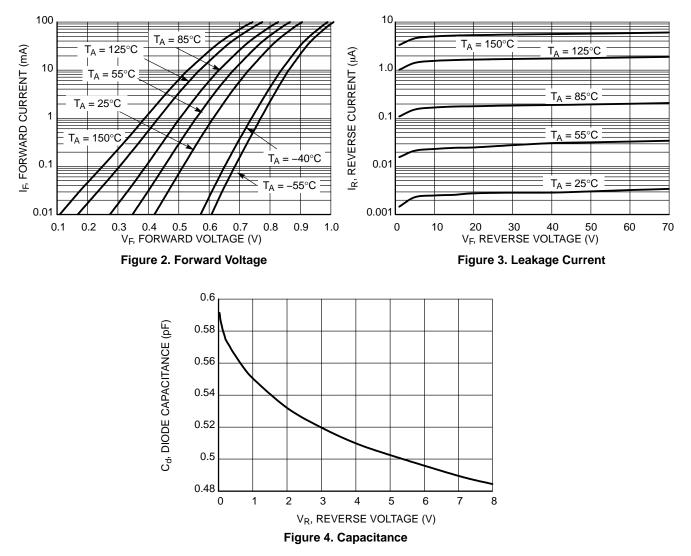
Notes: 1. A 2.0 k variable resistor adjusted for a Forward Current (I_F) of 10 mA. 2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 10 mA.

3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

BAV70L, SBAV70L

Curves Applicable to Each Anode



MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

D

3

TOP VIEW

SIDE VIEW

Нe

-3X b

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SCALE 4:1

A____ ' A1SOT-23 (TO-236) CASE 318 ISSUE AT

0.25

-L1

DETAIL A

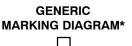
END VIEW

DATE 01 MAR 2023

NDTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

| | MILLIMETERS | | INCHES | | | |
|----------------|-------------|------|--------|-------|-------|-------|
| DIM | MIN. | NDM. | MAX. | MIN. | NDM. | MAX. |
| Α | 0.89 | 1.00 | 1.11 | 0.035 | 0.039 | 0.044 |
| A1 | 0.01 | 0.06 | 0.10 | 0.000 | 0.002 | 0.004 |
| b | 0.37 | 0.44 | 0.50 | 0.015 | 0.017 | 0.020 |
| с | 0.08 | 0.14 | 0.20 | 0.003 | 0.006 | 0.008 |
| D | 2.80 | 2.90 | 3.04 | 0.110 | 0.114 | 0.120 |
| E | 1.20 | 1.30 | 1.40 | 0.047 | 0.051 | 0.055 |
| e | 1.78 | 1.90 | 2.04 | 0.070 | 0.075 | 0.080 |
| L | 0.30 | 0.43 | 0.55 | 0.012 | 0.017 | 0.022 |
| L1 | 0.35 | 0.54 | 0.69 | 0.014 | 0.021 | 0.027 |
| H _E | 2.10 | 2.40 | 2.64 | 0.083 | 0.094 | 0.104 |
| Т | 0* | | 10* | 0* | | 10* |



DETAIL A



- XXX = Specific Device Code
- M = Date Code
- = Pb–Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

STYLES ON PAGE 2

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| DESCRIPTION: SOT-23 (TO-236) | | PAGE 1 OF 2 | | | | |
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MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

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SOT-23 (TO-236) CASE 318 ISSUE AT

DATE 01 MAR 2023

| STYLE 1 THRU 5: CANCELLED | STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR | STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR | STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE | | |
|---|---|---|--|------------------|------------------|
| STYLE 9: | STYLE 10: | STYLE 11: | STYLE 12: | STYLE 13: | STYLE 14: |
| PIN 1. ANODE | PIN 1. DRAIN | PIN 1. ANODE | PIN 1. CATHODE | PIN 1. SOURCE | PIN 1. CATHODE |
| 2. ANODE | 2. SOURCE | 2. CATHODE | 2. CATHODE | 2. DRAIN | 2. GATE |
| 3. CATHODE | 3. GATE | 3. CATHODE-ANODE | 3. ANODE | 3. GATE | 3. ANODE |
| STYLE 15: | STYLE 16: | STYLE 17: | STYLE 18: | STYLE 19: | STYLE 20: |
| PIN 1. GATE | PIN 1. ANODE | PIN 1. NO CONNECTION | PIN 1. NO CONNECTION | PIN 1. CATHODE | PIN 1. CATHODE |
| 2. CATHODE | 2. CATHODE | 2. ANODE | 2. CATHODE | 2. ANODE | 2. ANODE |
| 3. ANODE | 3. CATHODE | 3. CATHODE | 3. ANODE | 3. CATHODE-ANODE | 3. GATE |
| STYLE 21: | STYLE 22: | STYLE 23: | STYLE 24: | STYLE 25: | STYLE 26: |
| PIN 1. GATE | PIN 1. RETURN | PIN 1. ANODE | PIN 1. GATE | PIN 1. ANODE | PIN 1. CATHODE |
| 2. SOURCE | 2. OUTPUT | 2. ANODE | 2. DRAIN | 2. CATHODE | 2. ANODE |
| 3. DRAIN | 3. INPUT | 3. CATHODE | 3. SOURCE | 3. GATE | 3. NO CONNECTION |
| STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE | STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE | | | | |

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